

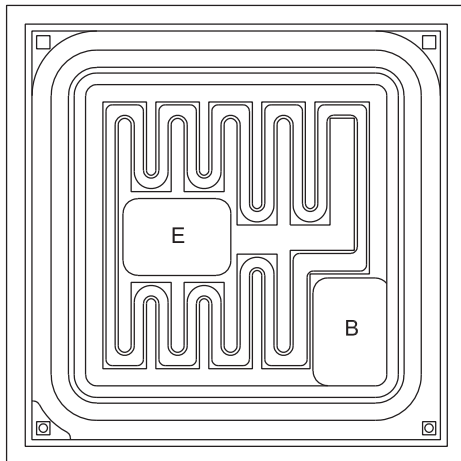
**PROCESS CP304**  
**Small Signal Transistor**  
NPN - High Current Transistor Chip



**PROCESS DETAILS**

Process	EPITAXIAL PLANAR
Die Size	22 x 22 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	5.7 x 3.9 MILS
Emitter Bonding Pad Area	5.3 x 3.9 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

**GEOMETRY**



BACKSIDE COLLECTOR R1

**GROSS DIE PER 4 INCH WAFER**

22,400

**PRINCIPAL DEVICE TYPES**

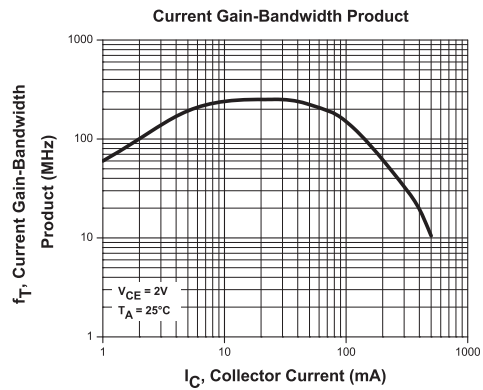
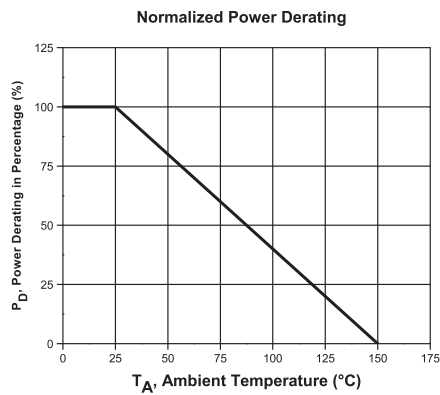
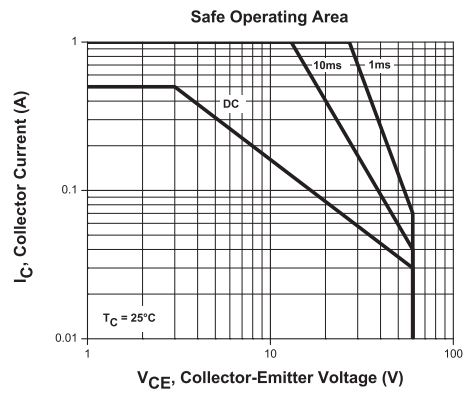
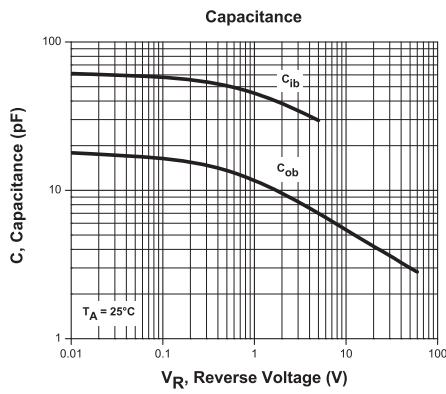
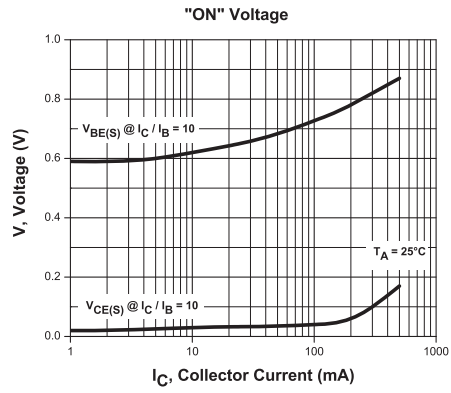
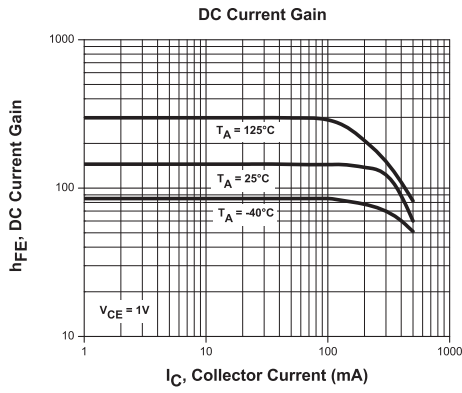
MPSA05

MPSA06

R4 (22-March 2010)

# PROCESS CP304

## Typical Electrical Characteristics



R4 (22-March 2010)